

Sheet 1 of 1

FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT(S)  
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ATTY DOCKET NO. **BHT/3230-63** APPLICATION NO. **10/625,516**

APPLICANT **TSUI**

FILING DATE **July 24, 2003** GROUP **2813**

Date Submitted to PTO: **August 2, 2004** U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

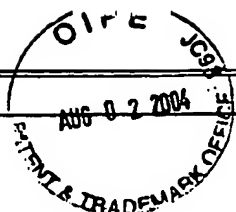
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

<b>CAT</b>	C.J. Koeneke, et al.; "Schottky MOSFET for VLSI"; in Dig. of IEDM, p. 367; 1981
<b>CAT</b>	S.E. Swirhun et al.; "A VLSI Suitable Schottky Barrier CMOS Process"; IEEE, Trans. Electron Devices; Vol. ED-32, No. 2; p. 194; 1985
<b>CAT</b>	B.Y. Tsui et al.; "A Novel Process For High-Performance Schottky Barrier PMOS"; J. Electrochem. Soc.; Vol. 136, No. 5; p. 1456; 1989
<b>CAT</b>	C. Wang et al.; "Sub-50-nm PtSi Schottky Source/Drain p-MOSFETs"; in Proc. of Device Research Conf.; p.72; 1998
<b>CAT</b>	C. Wang et al.; "Sub-50-nm PtSi Schottky Source/Drain Metal-Oxide-Semiconductor Field-Effect Transistors; Appl. Phys. Lett.; Vol. 74, No. 8; p. 1174; 1999
<b>CAT</b>	W. Saitoh et al. ; "35 nm Metal Gate SOI-p-MOSFETs With PtSi Schottky Source/Drain"; In Proc. of Device Research Conf.; p. 30; 1999
<b>CAT</b>	A. Itoh et al.; "Very Short Channel Metal-Gate Schottky Source/Drain SOI-PMOSFETs And Their Short Channel Effect"; in Proc. of Device Research Conf.; p. 77; 2000
<b>CAT</b>	H.C. Lin et al.; "A Novel Implantless MOS Thin-Film Transistor With Simple Processing, Excellent Performance, and Ambipolar Operation Capability"; in Dig. of IEDM; p. 857; 2000
<b>CAT</b>	K. Uchida et al.; "Enhancement Of Hot-Electron Generation Rate in Schottky Source Metal-Oxide-Semiconductor Field-Effect Transistors"; Appl. Phys. Lett.; Vol. 76, No. 26; p. 3992; 2000

EXAMINER **Craig A. Thompson**

DATE CONSIDERED **8/20/04**

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